

256 Mbit Consumer FCRAM™

1.8 V, ×32, Low Power DDR SDRAM, SiP-oriented

MB81EDS253245

■ FEATURES

- RAM featuring low power consumption and high-speed data transfer
- Low Power DDR SDRAM interface
- 2M-word × 32bit × 4-bank organization
- 1.8V Power Supply ($V_{DD}=V_{DDQ}$)
- Junction Temperature $T_J = -10^{\circ}\text{C}$ to $+105^{\circ}\text{C}$
- Clock stop capability during idle period
- Auto precharge option for each burst access
- Configurable Driver Strength and Pre Driver Strength
- Auto Refresh and Self Refresh Modes
- Deep Power Down Mode

■ MAIN SPECIFICATIONS

Part Number	MB81EDS253245
Organization	2 M Word × 32 bit × 4-bank
Interface	Low Power DDR
Supply Voltage	1.7 V to 1.95 V
Burst Operating Frequency (Max.)	216 MHz
Data Transfer Rate (Max.)	1.73 Gbytes / s
CLK Access Time (Min.)	4.6 ns
Active Current (Burst Read) (Max.)	235 mA
Deep Power Down Current (Max.)	20 μA

Note: FCRAM is a trademark of FUJITSU MICROELECTRONICS LIMITED, Japan.